

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



In re application of

Hiroyuki KIYOKU, *et al.*

Continuation of Application No. 09/603,437

Group Art Unit: 1765

Confirmation No.: To be Assigned

Examiner: To be Assigned

Filed: November 6, 2001

For: NITRIDE SEMICONDUCTOR GROWTH METHOD, NITRIDE SEMICONDUCTOR  
SUBSTRATE, AND NITRIDE SEMICONDUCTOR DEVICE

INFORMATION DISCLOSURE STATEMENT  
UNDER 37 C.F.R. §§ 1.97 and 1.98

Commissioner for Patents  
Washington, D.C. 20231

Sir:

In accordance with the duty of disclosure under 37 CFR §1.56, Applicants hereby notify the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO-1449 forms which are all the references submitted in parent application No. 09/603,437. Applicants are not submitting duplicate copies of these references but requests that they be listed on the face of any patent granted on the above application. (*See* 37 CFR §1.98(d)).

The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicants do not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a competent reference against the claims of the present application.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "Edward F. Kenahan".

Edward F. Kenahan  
Registration No. 28,962  
David A. Klein  
Registration No. 46,835

SUGHRUE MION, PLLC  
2100 Pennsylvania Avenue, N.W.  
Washington, D.C. 20037-3213  
Telephone: (202) 293-7060  
Facsimile: (202) 293-7860

Date: November 8, 2001

<b>Form PTO-1449</b> <b>(Rev. 2-32)</b>		<b>U.S. Department of Commerce</b> <b>Patent &amp; Trademark Office</b>		Atty. Docket No.  Q66212		Serial No.:  Confirmation No.: To be Assigned	
<b>INFORMATION DISCLOSURE STATEMENT</b> (Use several sheets if necessary)				Applicant: Hiroyuki KIYOKU, <i>et al.</i>			
				Filing Date: 11/8/2001		Group: 1765	

CS97 U.S. PTO  
 09/986332  
 1/08/01

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

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